Motion and Recombination of Electrons and Holes

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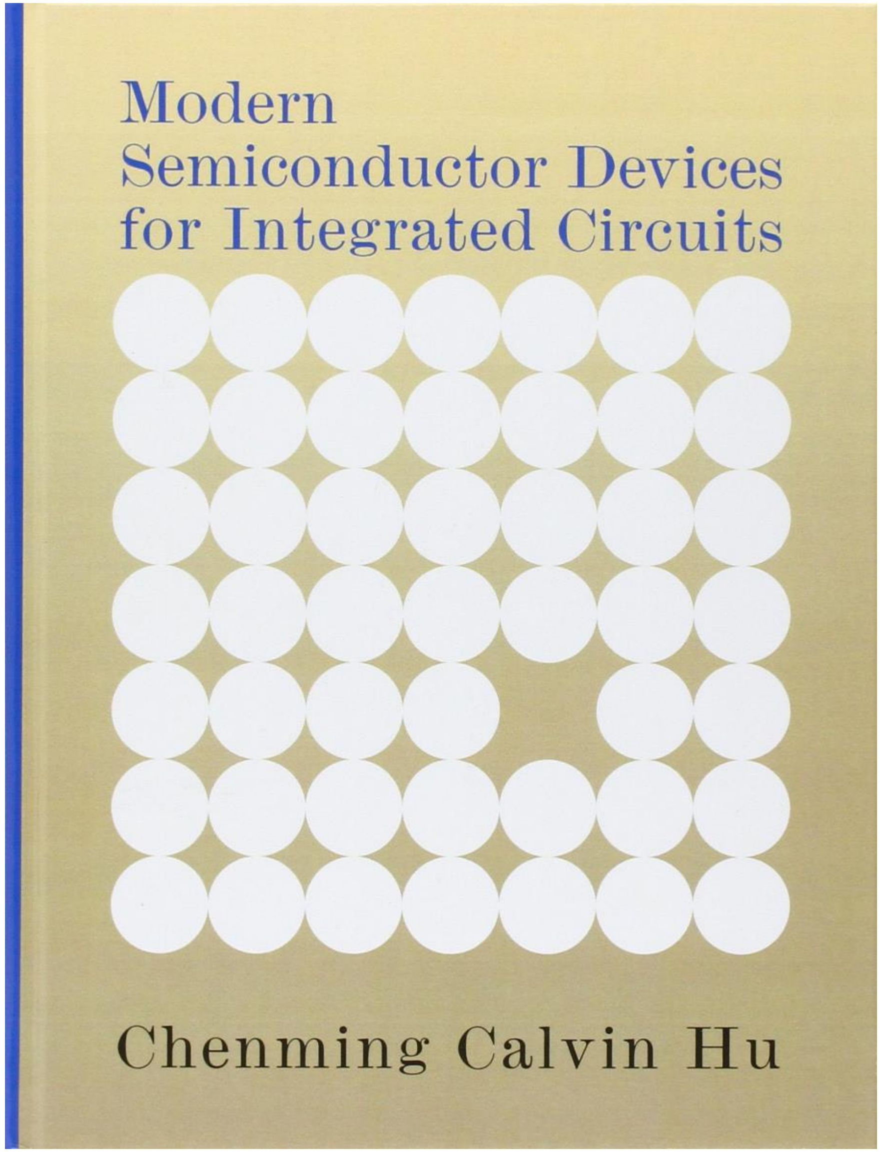
Chapter 2

Motion and Recombination of Electrons and Holes



Chapter 2 Motion and Recombination of Electrons and Holes

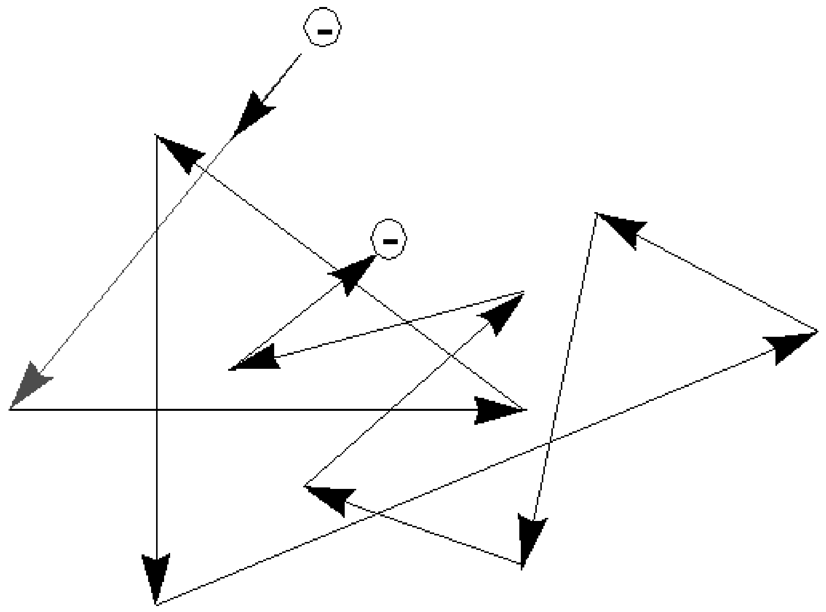
2.1 Thermal Motion

Average electron or hole kinetic energy $= \frac{3}{2}kT = \frac{1}{2}mv_{th}^2$

$$v_{th} = \sqrt{\frac{3kT}{m_{eff}}} = \sqrt{\frac{3 \times 1.38 \times 10^{-23}\,\text{JK}^{-1} \times 300\ \text{K}}{0.26 \times 9.1 \times 10^{-31}\,\text{kg}}}$$

$$= 2.3 \times 10^{5}\ \text{m/s} = 2.3 \times 10^{7}\ \text{cm/s}$$

2.1 Thermal Motion



- Zig-zag motion is due to collisions or scattering with imperfections in the crystal.
- Net thermal velocity is zero.
- Mean time between collisions is $\tau_m \sim 0.1\text{ps}$

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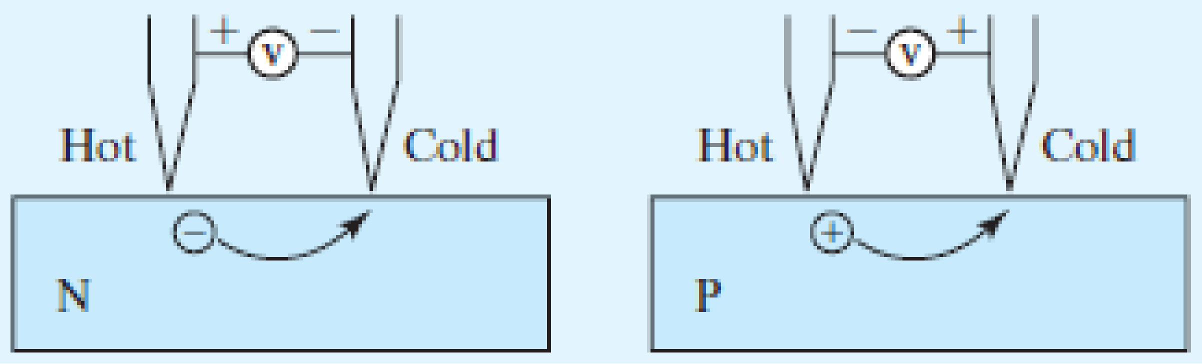
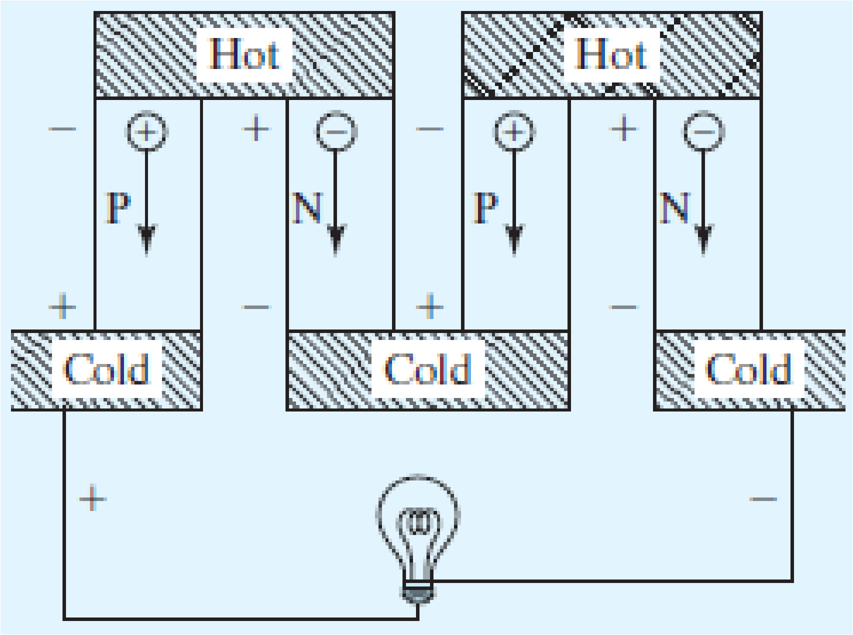
Hot-point Probe can determine sample doing type



***Hot-point Probe** distinguishes N and P type semiconductors.*

***Thermoelectric Generator** (from heat to electricity) and Cooler (from electricity to refrigeration)*



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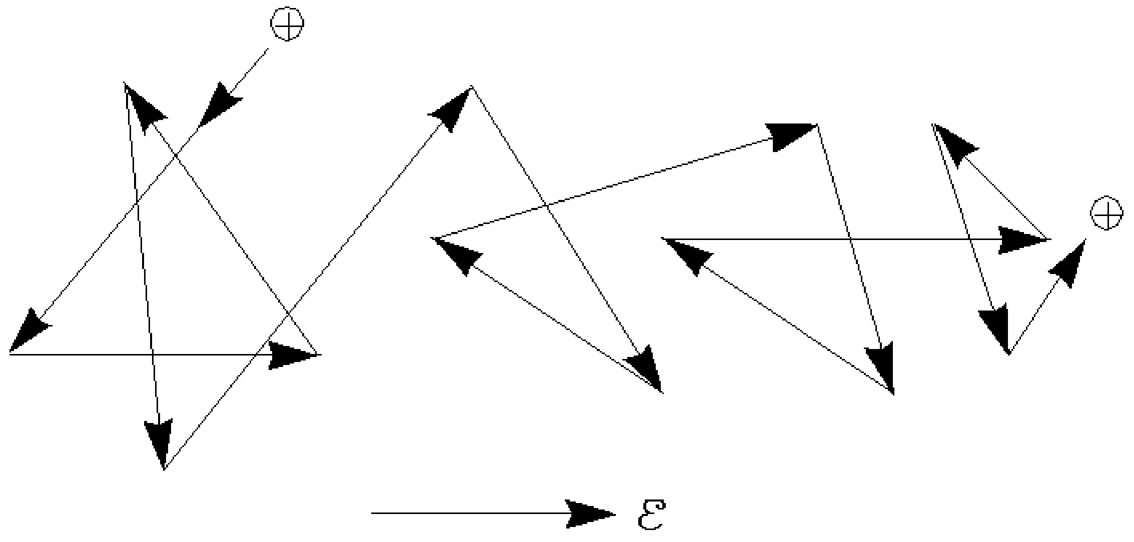
2.2 Drift

2.2.1 Electron and Hole Mobilities



- ***Drift*** is the motion caused by an electric field.

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2.2.1 Electron and Hole Mobilities

$$m_p v = q \mathbf{E} \tau_{mp}$$

$$v = \frac{q \mathbf{E} \tau_{mp}}{m_p}$$

$$v = \mu_p \mathbf{E}$$

$$\mu_p = \frac{q \tau_{mp}}{m_p}$$

$$v = -\mu_n \mathbf{E}$$

$$\mu_n = \frac{q \tau_{mn}}{m_n}$$

- μ_p is the hole mobility and μ_n is the electron mobility

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2.2.1 Electron and Hole Mobilities

$$v = \mu \mathbf{E}; \quad \mu \text{ has the dimensions of } v/\mathbf{E} \left[\frac{\text{cm/s}}{\text{V/cm}} = \frac{\text{cm}^2}{\text{V} \cdot \text{s}}\right].$$

Electron and hole mobilities of selected semiconductors

	Si	**Ge**	**GaAs**	**InAs**
μ_n (cm^2/V·s)	1400	3900	8500	30000
μ_p (cm^2/V·s)	470	1900	400	500

Based on the above table alone, which semiconductor and which carriers (electrons or holes) are attractive for applications in high-speed devices?

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Drift Velocity, Mean Free Time, Mean Free Path

EXAMPLE: *Given μ_p = 470 cm²/V·s, what is the hole drift velocity at* **E** *= 10^3 V/cm? What is τ_{mp} and what is the distance traveled between collisions (called the* ***mean free path****)? Hint: When in doubt, use the MKS system of units.*

Solution: $v = \mu_p \mathbf{E} = 470\ \text{cm}^2/\text{V·s} \times 10^3\ \text{V/cm} = 4.7\times 10^5\ \text{cm/s}$

$$\tau_{mp} = \mu_p m_p/q = 470\ \text{cm}^2/\text{V·s} \times 0.39 \times 9.1\times10^{-31}\ \text{kg}/1.6\times10^{-19}\ \text{C}$$

$$= 0.047\ \text{m}^2/\text{V·s} \times 2.2\times10^{-12}\ \text{kg/C} = 1\times10^{-13}\text{s} = 0.1\ \text{ps}$$

$$\textit{mean free path} = \tau_{mh} v_{th} \sim 1\times 10^{-13}\ \text{s} \times 2.2\times10^{7}\ \text{cm/s}$$

$$= 2.2\times10^{-6}\ \text{cm} = 220\ \text{Å} = 22\ \text{nm}$$

This is smaller than the typical dimensions of devices, but getting close.

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2.2.2 Mechanisms of Carrier Scattering

There are two main causes of carrier scattering:

1. Phonon Scattering
2. Ionized-Impurity (Coulombic) Scattering

Phonon scattering mobility decreases when temperature rises:

$$\mu_{phonon} \propto \tau_{phonon} \propto \frac{1}{phonon \quad density \times carrier \quad thermal \quad velocity} \propto \frac{1}{T \times T^{1/2}} \propto T^{-3/2}$$

$\mu = q\tau/m$

$\propto T$

$v_{th} \propto T^{1/2}$

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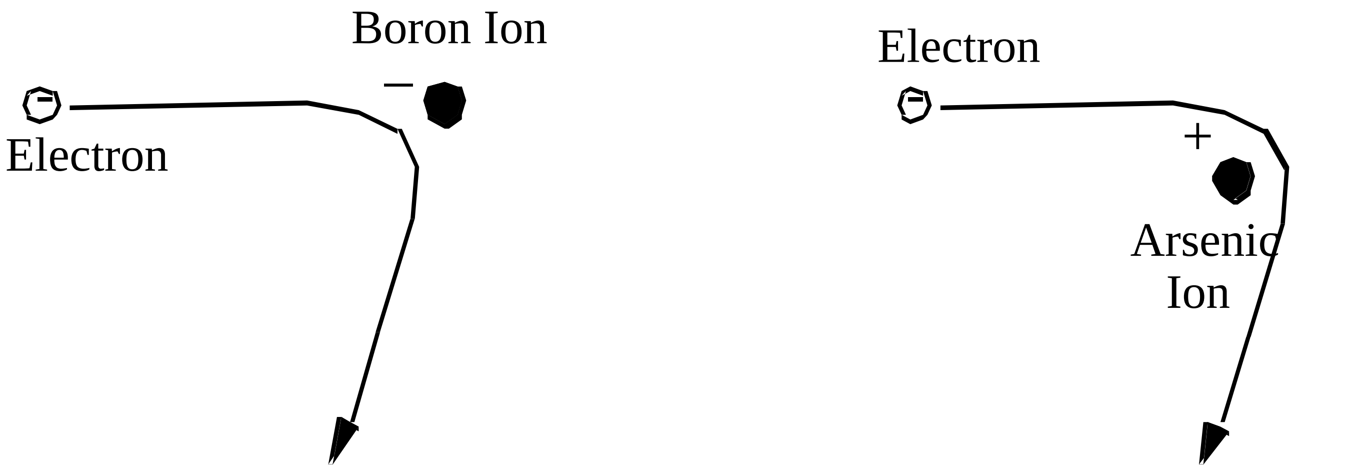
Impurity (Dopant)-Ion Scattering or Coulombic Scattering



There is less change in the direction of travel if the electron zips by the ion at a higher speed.

$$\mu_{impurity} \propto \frac{v_{th}^{3}}{N_a + N_d} \propto \frac{T^{3/2}}{N_a + N_d}$$

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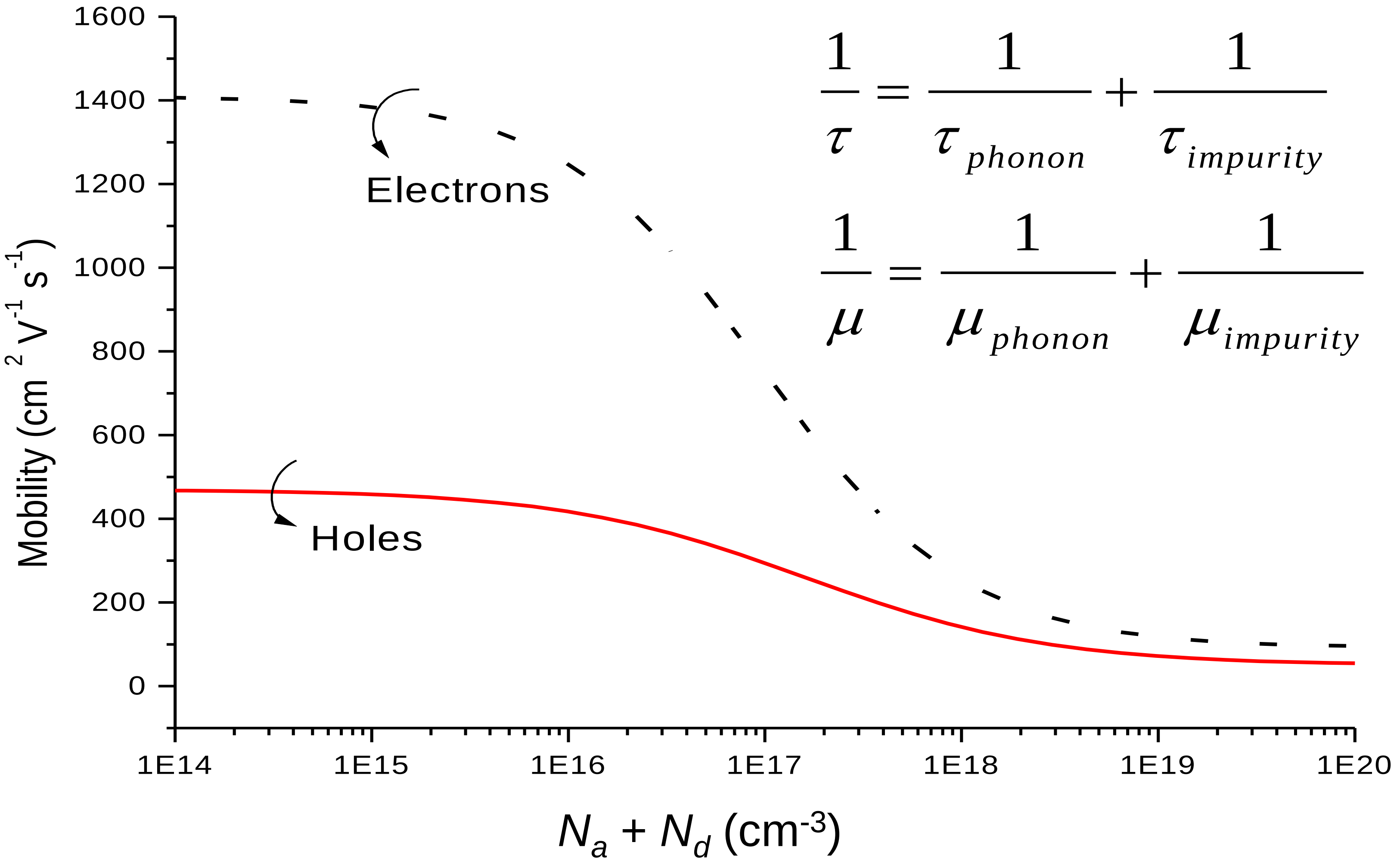
Total Mobility



$$\frac{1}{\tau} = \frac{1}{\tau_{phonon}} + \frac{1}{\tau_{impurity}}$$

$$\frac{1}{\mu} = \frac{1}{\mu_{phonon}} + \frac{1}{\mu_{impurity}}$$

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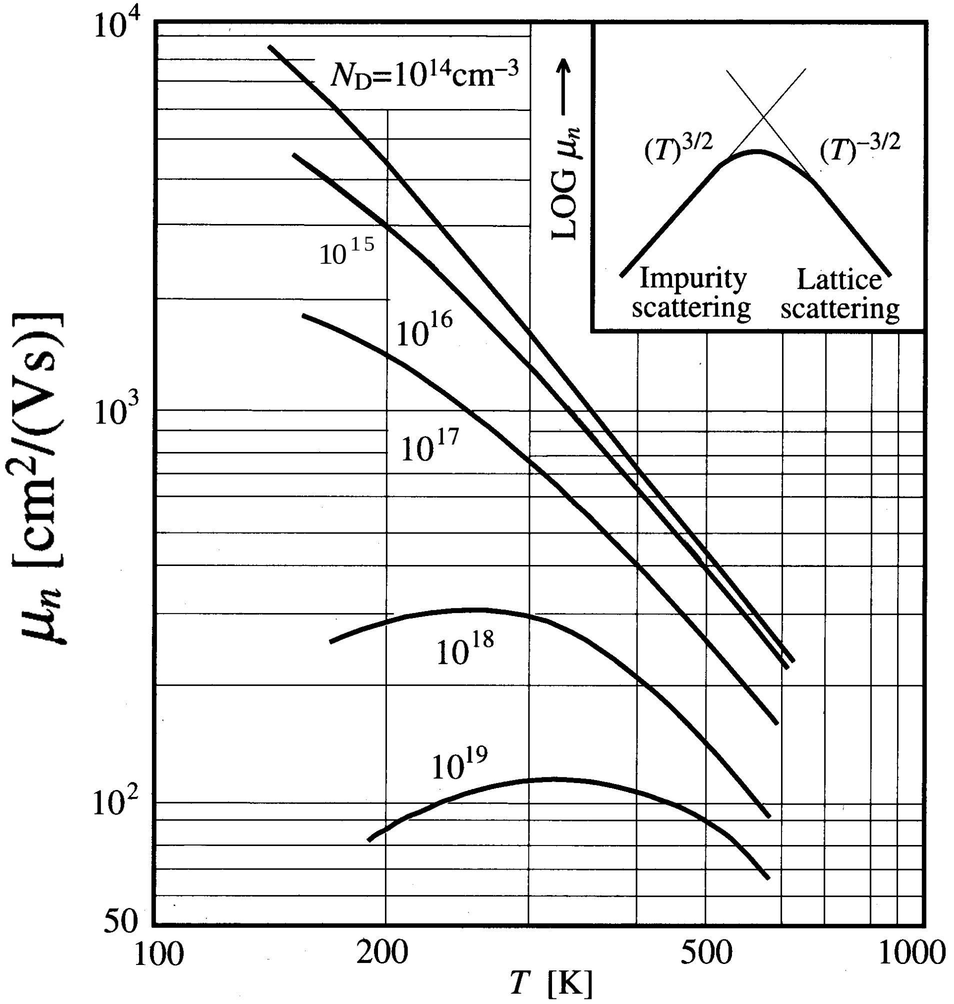
Temperature Effect on Mobility



Question:
What N_d will make $d\mu_n/dT = 0$ at room temperature?

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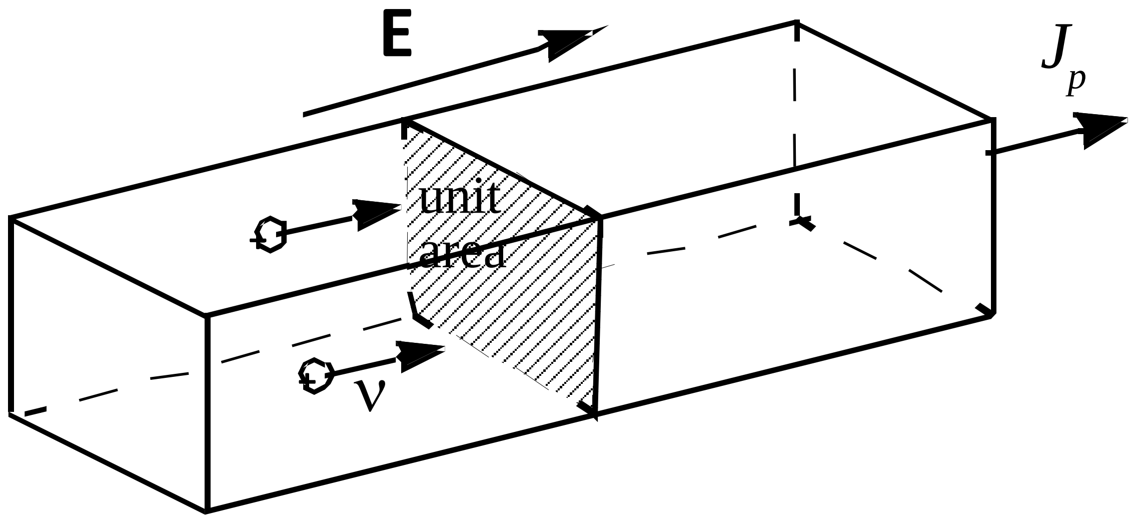
Velocity Saturation

- When the kinetic energy of a carrier exceeds a critical value, it generates an optical phonon and loses the kinetic energy.
- Therefore, the kinetic energy is capped at large **E,** and the velocity does not rise above a saturation velocity, v_{sat} .
- ***Velocity saturation*** has a deleterious effect on device speed as shown in Ch. 6.

2.2.3 Drift Current and Conductivity



Hole current density $\boxed{J_p = qpv}$ A/cm^2 or C/cm^2·sec

EXAMPLE: If p = 10^{15}cm^{-3} and v = 10^4 cm/s, then

$$J_p = 1.6\times10^{-19}\text{C} \times 10^{15}\text{cm}^{-3} \times 10^4\text{cm/s}$$

$$= 1.6\ \text{C/s}\cdot\text{cm}^2 = 1.6\ \text{A/cm}^2$$

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2.2.3 Drift Current and Conductivity

$$J_{p,drift} = qpv = qp\mu_p \mathbf{E}$$

$$J_{n,drift} = -qnv = qn\mu_n \mathbf{E}$$

$$J_{drift} = J_{n,drift} + J_{p,drift} = \sigma \mathbf{E} = (qn\mu_n + qp\mu_p)\mathbf{E}$$

$\therefore$ ***conductivity*** *(1/ohm-cm) of a semiconductor is*

$$\sigma = qn\mu_n + qp\mu_p$$

$1/\sigma$ = is resistivity (ohm-cm)

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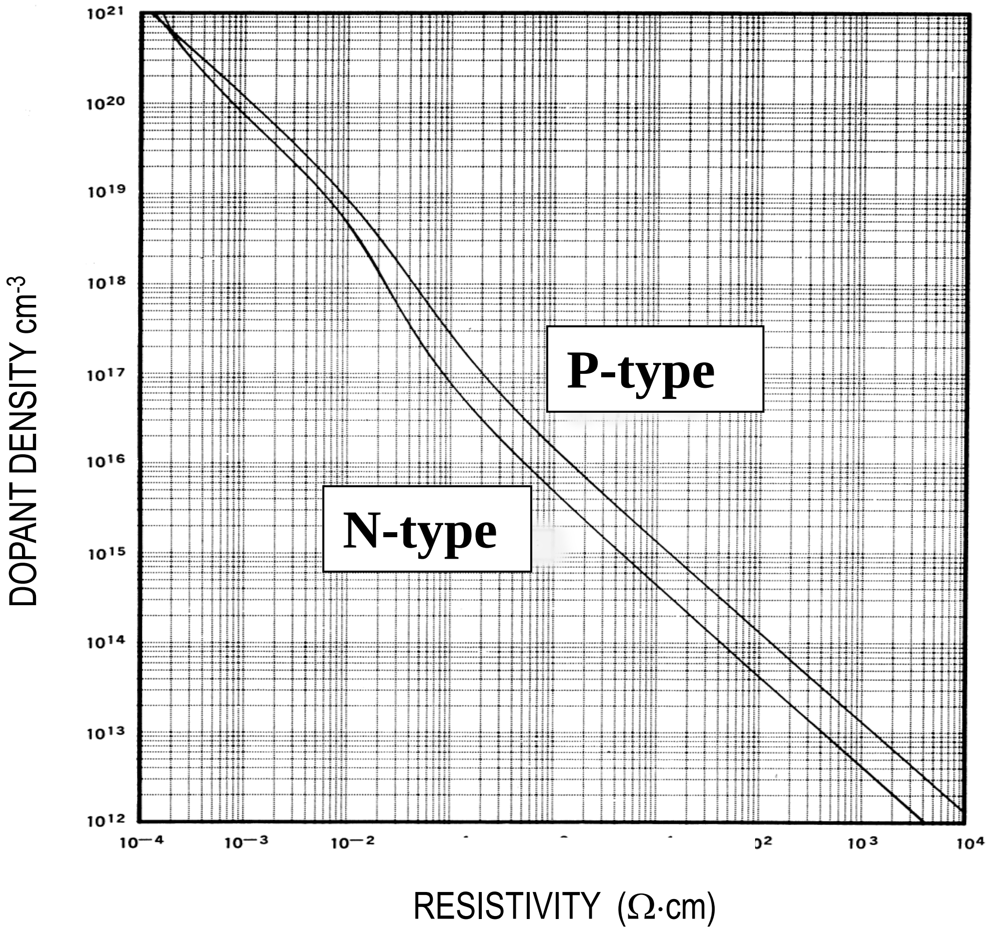
Relationship between Resistivity and Dopant Density



$$\rho = 1/\sigma$$

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EXAMPLE: Temperature Dependence of Resistance

(a) What is the resistivity (ρ) of silicon doped with $10^{17}cm^{-3}$ of arsenic?

(b) What is the resistance (R) of a piece of this silicon material 1μm long and 0.1 μm^2 in cross-sectional area?

Solution:

(a) Using the N-type curve in the previous figure, we find that ρ = 0.084 Ω-cm.

$$(b)\ R = \rho L/A = 0.084\ \Omega\text{-cm} \times 1\ \mu\text{m} / 0.1\ \mu\text{m}^2$$
$$= 0.084\ \Omega\text{-cm} \times 10^{-4}\ \text{cm}/ 10^{-10}\ \text{cm}^2$$
$$= 8.4 \times 10^{-4}\ \Omega$$

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EXAMPLE: Temperature Dependence of Resistance

By what factor will R increase or decrease from T=300 K to T=400 K?

Solution: *The temperature dependent factor in σ (and therefore ρ) is μ_n. From the mobility vs. temperature curve for 10^{17}cm^{-3}, we find that μ_n decreases from 770 at 300K to 400 at 400K. As a result, R* ***increases*** *by*

$$\frac{770}{400} = 1.93$$

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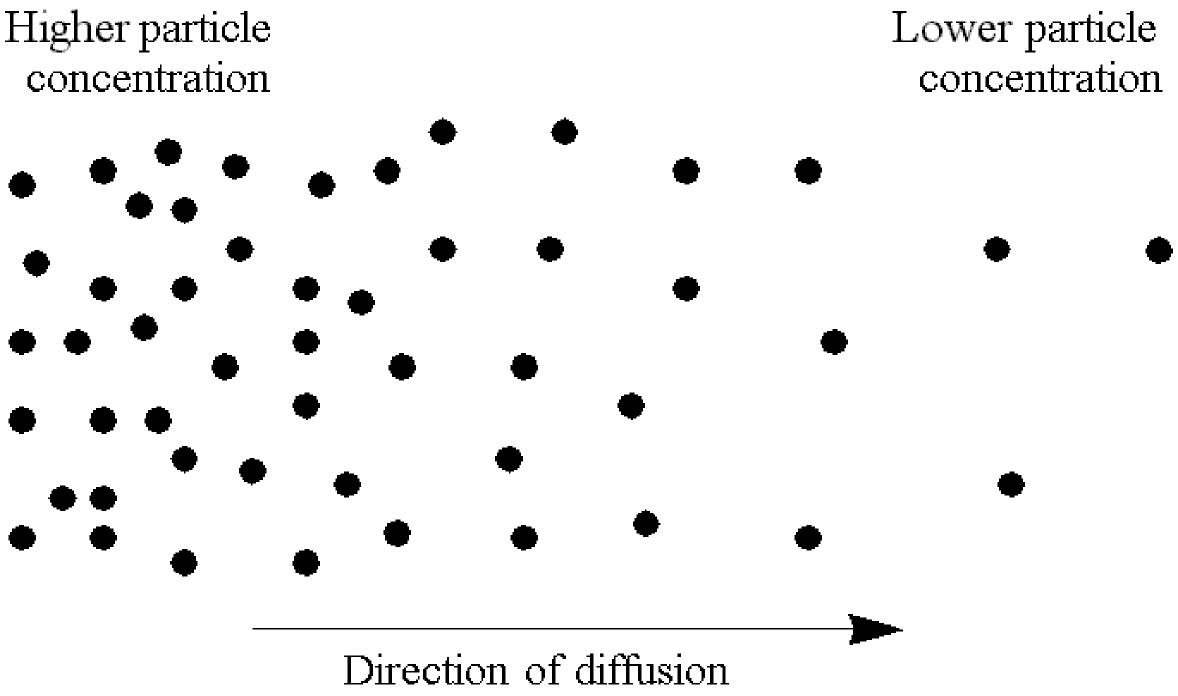
2.3 Diffusion Current



Particles diffuse from a higher-concentration location to a lower-concentration location.

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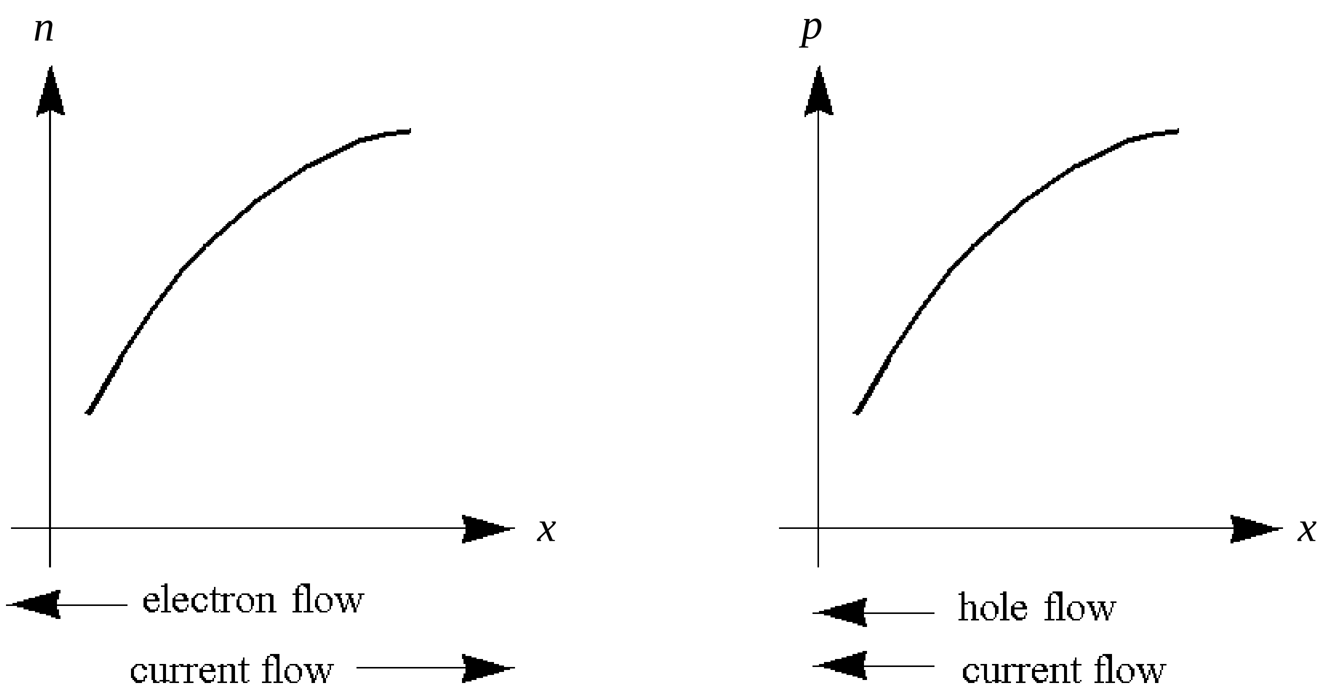
2.3 Diffusion Current

$$J_{n,diffusion} = qD_n \frac{dn}{dx} \qquad J_{p,diffusion} = -qD_p \frac{dp}{dx}$$

D is called the diffusion constant. Signs explained:



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Total Current – Review of Four Current Components

$$J_{TOTAL} = J_n + J_p$$

$$J_n = J_{n,drift} + J_{n,diffusion} = qn\mu_n\mathbf{E} + qD_n\frac{dn}{dx}$$

$$J_p = J_{p,drift} + J_{p,diffusion} = qp\mu_p\mathbf{E} - qD_p\frac{dp}{dx}$$

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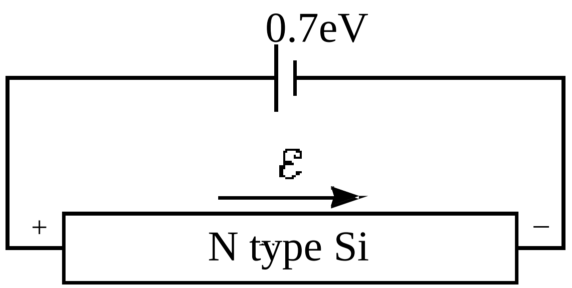
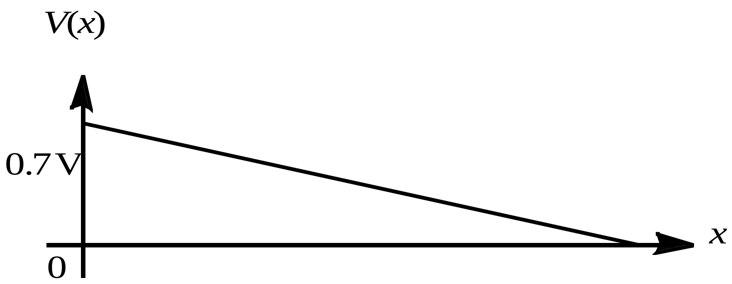
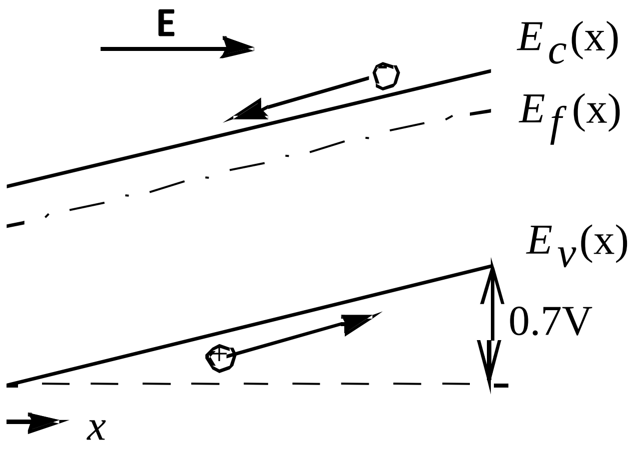
2.4 Relation Between the Energy Diagram and V, E





E_c and E_v vary in the opposite direction from the voltage. That is, E_c and E_v are higher where the voltage is lower.

$$\mathbf{E}(x) = -\frac{dV}{dx} = \frac{1}{q}\frac{dE_c}{dx} = \frac{1}{q}\frac{dE_v}{dx}$$



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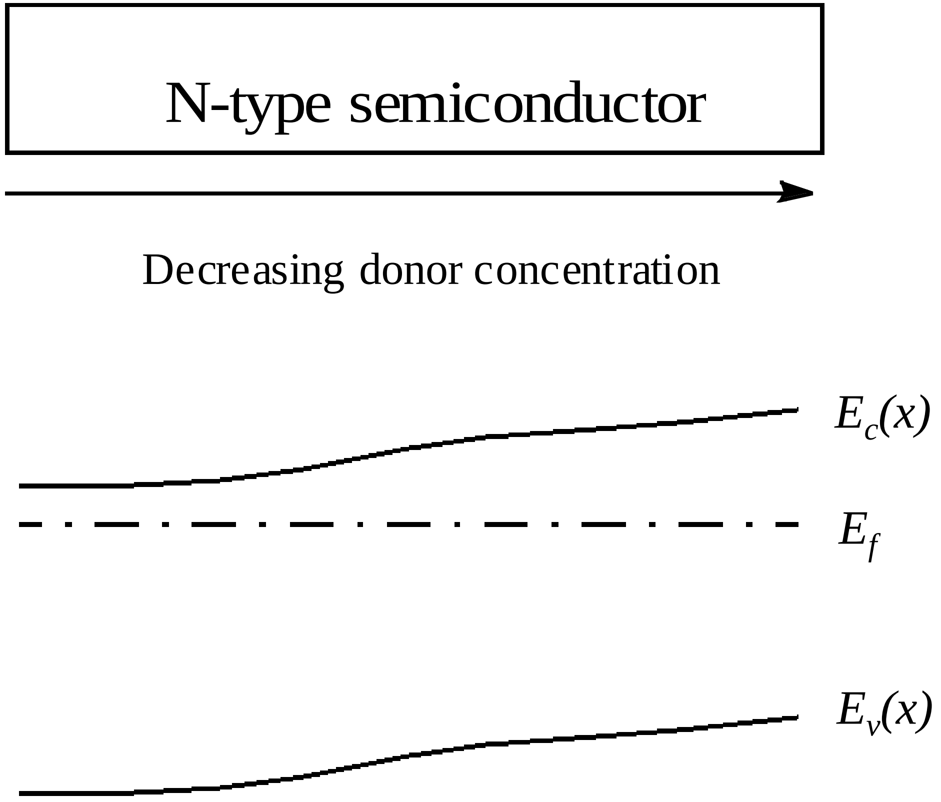
2.5 *Einstein Relationship between D and μ*

Consider a piece of non-uniformly doped semiconductor.



$$n = N_c e^{-(E_c - E_f)/kT}$$

$$\frac{dn}{dx} = -\frac{N_c}{kT} e^{-(E_c - E_f)/kT} \frac{dE_c}{dx}$$

$$= -\frac{n}{kT}\frac{dE_c}{dx}$$

$$= -\frac{n}{kT} q \mathbf{E}$$

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2.5 Einstein Relationship between D and μ

$$\frac{dn}{dx} = -\frac{n}{kT} q\mathbf{E}$$

$$J_n = qn\mu_n\mathbf{E} + qD_n\frac{dn}{dx} = 0 \quad \text{at equilibrium.}$$

$$0 = qn\mu_n\mathbf{E} - qn\frac{qD_n}{kT}\mathbf{E}$$

$$\boxed{D_n = \frac{kT}{q}\mu_n} \quad \text{Similarly,} \quad \boxed{D_p = \frac{kT}{q}\mu_p}$$

These are known as the Einstein relationship.

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EXAMPLE: Diffusion Constant

What is the hole diffusion constant in a piece of silicon with μ_p = 410 cm^2 V^{-1}s^{-1} ?

Solution:

$$D_p = \left(\frac{kT}{q}\right)\mu_p = (26\ \text{mV})\cdot 410\ \text{cm}^2\text{V}^{-1}\text{s}^{-1} = 11\,\text{cm}^2/\text{s}$$

Remember: kT/q = 26 mV at room temperature.

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2.6 Electron-Hole Recombination

- The equilibrium carrier concentrations are denoted with n_0 and p_0.
- The total electron and hole concentrations can be different from n_0 and p_0 .
- *T*he differences are called the ***excess carrier concentrations*** n' and p'.

$$n \equiv n_0 + n'$$
$$p \equiv p_0 + p'$$

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Charge Neutrality

- Charge neutrality is satisfied at equilibrium ($n' = p' = 0$).
- When a non-zero n' is present, an equal p' may be assumed to be present to maintain charge equality and vice-versa.
- If charge neutrality is not satisfied, the net charge will attract or repel the (majority) carriers through the drift current until neutrality is restored.

$$n' = p'$$

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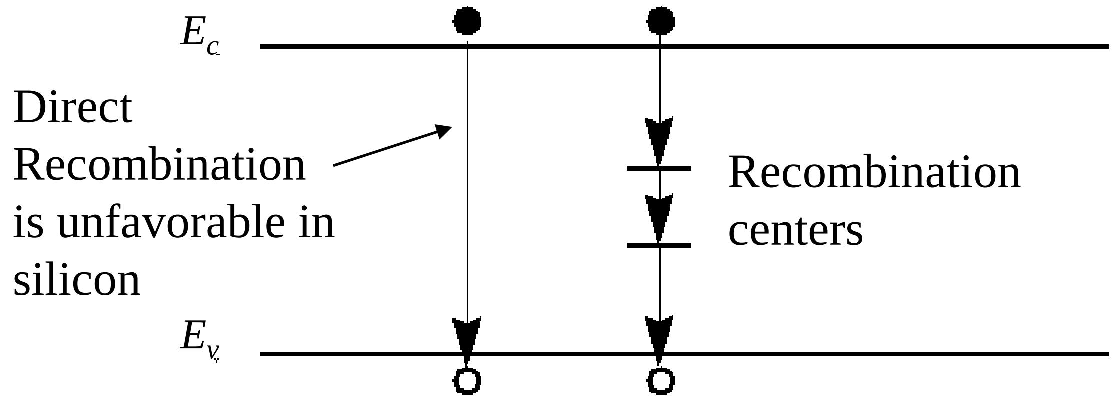
Recombination Lifetime

- Assume light generates *n'* and *p'*. If the light is suddenly turned off, *n'* and *p'* decay with time until they become zero.
- The process of decay is called ***recombination.***
- The time constant of decay is the ***recombination time*** or ***carrier lifetime,*** τ.
- Recombination is nature's way of restoring equilibrium ($n' = p' = 0$).

Recombination Lifetime

- τ ranges from 1ns to 1ms in Si and depends on the density of metal impurities (contaminants) such as Au and Pt.
- These ***deep traps*** capture electrons and holes to facilitate recombination and are called ***recombination centers.***



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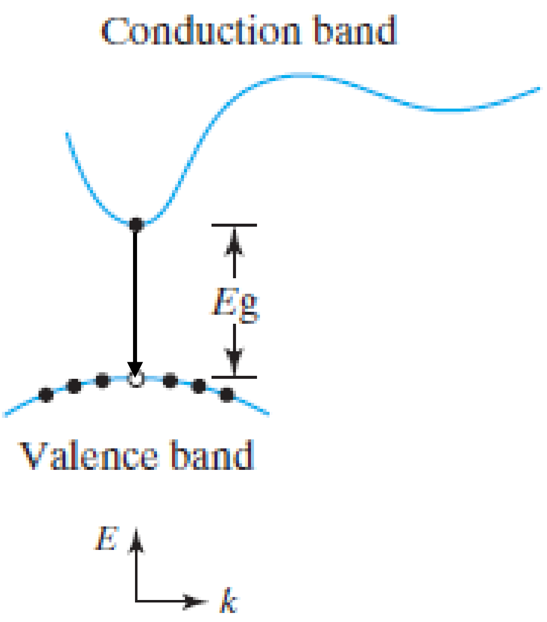
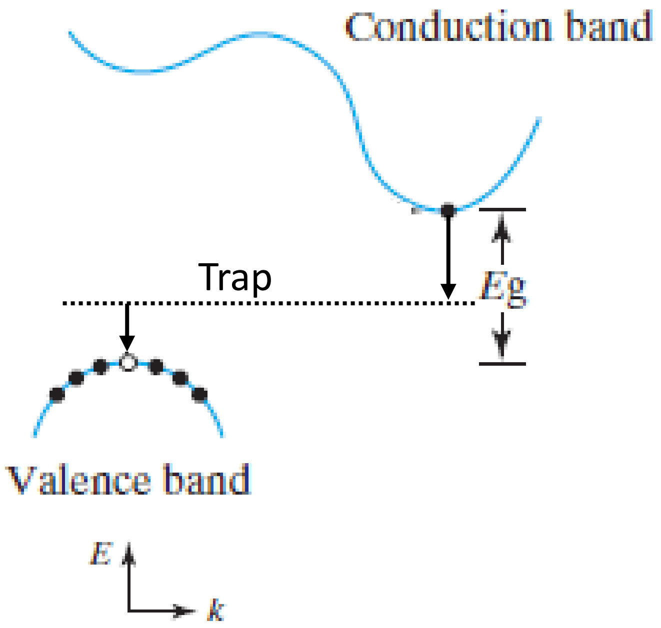
Direct and Indirect Band Gap





Direct band gap
Example: GaAs

Direct recombination is efficient as k conservation is satisfied.

Indirect band gap
Example: Si

Direct recombination is rare as k conservation is not satisfied

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Rate of recombination ($s^{-1}cm^{-3}$)

$$\frac{dn'}{dt} = -\frac{n'}{\tau}$$

$$n' = p'$$

$$\frac{dn'}{dt} = -\frac{n'}{\tau} = -\frac{p'}{\tau} = \frac{dp'}{dt}$$

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EXAMPLE: Photoconductors

A bar of Si is doped with boron at $10^{15}cm^{-3}$. It is exposed to light such that electron-hole pairs are generated throughout the volume of the bar at the rate of $10^{20}/s \cdot cm^3$. The recombination lifetime is $10\mu s$. What are (a) p_0 , (b) n_0 , (c) p', (d) n', (e) p , (f) n, and (g) the np product?

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EXAMPLE: Photoconductors

Solution:

(a) What is p_0?

$p_0 = N_a = 10^{15}\ \text{cm}^{-3}$

(b) What is n_0 ?

$n_0 = n_i^2/p_0 = 10^5\ \text{cm}^{-3}$

(c) What is p' ?

In steady-state, the rate of generation is equal to the rate of recombination.

$$10^{20}/\text{s-cm}^3 = p'/\tau$$

$$\therefore p' = 10^{20}/\text{s-cm}^3 \cdot 10^{-5}\text{s} = 10^{15}\ \text{cm}^{-3}$$

EXAMPLE: Photoconductors

(d) What is n'?

$n' = p' = 10^{15}$ cm^{-3}

(e) What is p?

$p = p_0 + p' = 10^{15}\text{cm}^{-3} + 10^{15}\text{cm}^{-3} = 2\times10^{15}\text{cm}^{-3}$

(f) What is n?

$n = n_0 + n' = 10^5\text{cm}^{-3} + 10^{15}\text{cm}^{-3} \sim 10^{15}\text{cm}^{-3}$ *since* $n_0 << n'$

(g) What is np?

$np \sim 2\times10^{15}\text{cm}^{-3} \cdot 10^{15}\text{cm}^{-3} = 2\times10^{30}\text{ cm}^{-6} >> n_i^2 = 10^{20}\text{ cm}^{-6}$.

The np product can be very different from n_i^2.

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2.7 Thermal Generation

If n' is negative, there are fewer electrons than the equilibrium value.

As a result, there is a net rate of ***thermal generation*** at the rate of $|n'|/\tau$.

2.8 Quasi-equilibrium and Quasi-Fermi Levels

- Whenever $n' = p' \neq 0$, $np \neq n_i^2$. We would like to preserve and use the simple relations:

$$n = N_c e^{-(E_c - E_f)/kT}$$

$$p = N_v e^{-(E_f - E_v)/kT}$$

- But these equations lead to $np = n_i^2$. The solution is to introduce two ***quasi-Fermi levels*** E_{fn} and E_{fp} such that

$$n = N_c e^{-(E_c - E_{fn})/kT}$$

$$p = N_v e^{-(E_{fp} - E_v)/kT}$$

Even when electrons and holes are not at equilibrium, *within each group* the carriers can be at equilibrium. Electrons are closely linked to other electrons but only loosely to holes.

EXAMPLE: Quasi-Fermi Levels and Low-Level Injection

Consider a Si sample with $N_d = 10^{17}$ cm^{-3} and $n' = p' = 10^{15}$ cm^{-3}.

(a) Find E_f.

$$n = N_d = 10^{17}\ \text{cm}^{-3} = N_c \exp[-(E_c - E_f)/kT]$$

$$\therefore\ E_c - E_f = 0.15\ \text{eV}. \quad (E_f \text{ is below } E_c \text{ by } 0.15\ \text{eV.})$$

Note: n' and p' are much less than the majority carrier concentration. This condition is called ***low-level injection.***

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EXAMPLE: Quasi-Fermi Levels and Low-Level Injection

Now assume $n' = p' = 10^{15}$ *cm*$^{-3}$.

(b) Find E_{fn} *and* E_{fp} .

$$n = 1.01\times10^{17}\text{cm}^{-3} = N_c e^{-(E_c - E_{fn})/kT}$$

$$\therefore\ E_c - E_{fn} = kT \times \ln(N_c/1.01\times10^{17}\text{cm}^{-3})$$
$$= 26\text{ meV} \times \ln(2.8\times10^{19}\text{cm}^{-3}/1.01\times10^{17}\text{cm}^{-3})$$
$$= 0.15\text{ eV}$$

E_{fn} is nearly identical to E_f because $n \approx n_0$.

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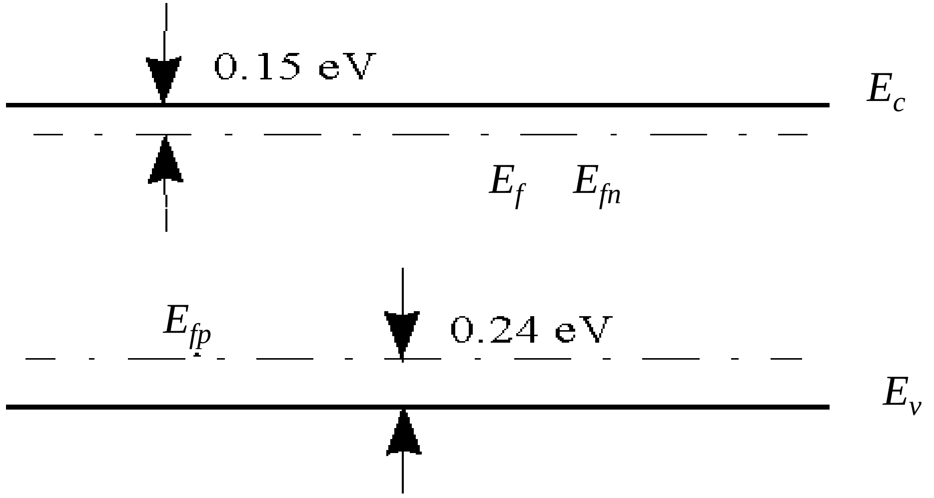
EXAMPLE: Quasi-Fermi Levels

$$p = 10^{15}\ \text{cm}^{-3} = N_v e^{-(E_{fp}-E_v)/kT}$$

$$\therefore\ E_{fp} - E_v = kT \times \ln(N_v/10^{15}\text{cm}^{-3})$$

$$= 26\ \text{meV} \times \ln(1.04\times10^{19}\text{cm}^{-3}/10^{15}\text{cm}^{-3})$$

$$= 0.24\ \text{eV}$$



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2.9 Chapter Summary

$$v_p = \mu_p \mathbf{E}$$

$$v_n = -\mu_n \mathbf{E}$$

$$J_{p,drift} = qp\mu_p \mathbf{E}$$

$$J_{n,drift} = qn\mu_n \mathbf{E}$$

$$J_{n,diffusion} = qD_n \frac{dn}{dx}$$

$$J_{p,diffusion} = -qD_p \frac{dp}{dx}$$

$$D_n = \frac{kT}{q}\mu_n$$

$$D_p = \frac{kT}{q}\mu_p$$

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2.9 Chapter Summary

τ is the recombination lifetime.

n' and p' are the ***excess carrier concentrations***.

$$n = n_0 + n'$$
$$p = p_0 + p'$$

Charge neutrality requires $n' = p'$.

$$\text{rate of recombination} = n'/\tau = p'/\tau$$

E_{fn} and E_{fp} are the quasi-Fermi levels of electrons and holes.

$$n = N_c e^{-(E_c - E_{fn})/kT}$$
$$p = N_v e^{-(E_{fp} - E_v)/kT}$$

Thank You